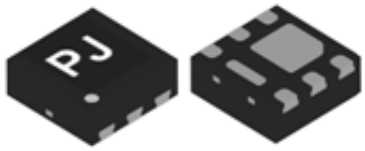
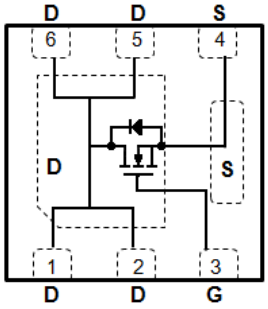
PJQ2408

30V N-Channel Enhancement Mode MOSFET

Voltage	30 V	Current	10 A

DFN2020B-6L





Features

- $R_{DS(ON)}$, V_{GS}@10V, I_D@10A<11.5mΩ
- $R_{DS(ON)}$, V_{GS}@4.5V, I_D@6A<15mΩ
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN2020B-6L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0003 ounces, 0.0086 grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (Note 4)		I_D	10	A
Pulsed Drain Current (Note 1)		I_{DM}	40	
Power Dissipation	T_A=25°C	P_D	2	W
	Derate above 25°C		16	mW/°C
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~150	°C
Typical Thermal Resistance - Junction to Ambient (Note 4,5)		$R_{\theta JA}$	62.5	°C/W

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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1	1.7	2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=10A	-	7.5	11.5	mΩ
		V_{GS}=4.5V, I_D=6A	-	11	15	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V_{DS}=15V, I_D=10A, V_{GS}=4.5V (Note 2,3)	-	6.9	-	nC
Gate-Source Charge	Q_{gs}		-	2.7	-	
Gate-Drain Charge	Q_{gd}		-	1.8	-	
Input Capacitance	Ciss	V_{DS}=25V, V_{GS}=0V, f=1MHZ	-	781	-	pF
Output Capacitance	Coss		-	158	-	
Reverse Transfer Capacitance	Crss		-	92	-	
Turn-On Delay Time	$td_{(on)}$	V_{DS}=15V, I_D=10A, V_{GS}=10V, R_G=6Ω (Note 2,3)	-	5.4	-	ns
Turn-On Rise Time	tr		-	86	-	
Turn-Off Delay Time	$td_{(off)}$		-	20	-	
Turn-Off Fall Time	tf		-	10	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	1.5	A
Diode Forward Voltage	V_{SD}	I_S=1A, V_{GS}=0V	-	0.73	1	V

NOTES :

1. Pulse width≤300us, Duty cycle≤2%.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
4. The maximum current rating is package limited.
5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch^2 with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

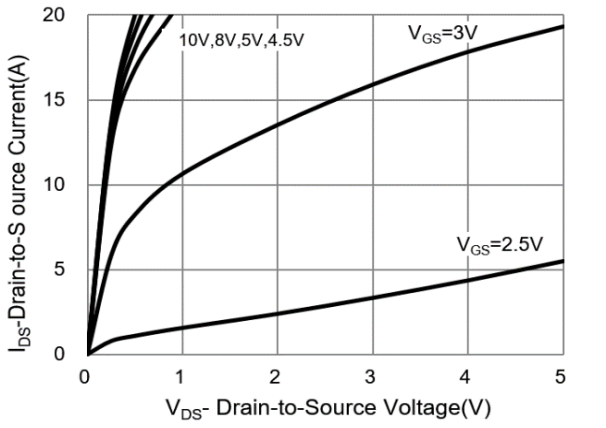

Fig.1 On-Region Characteristics

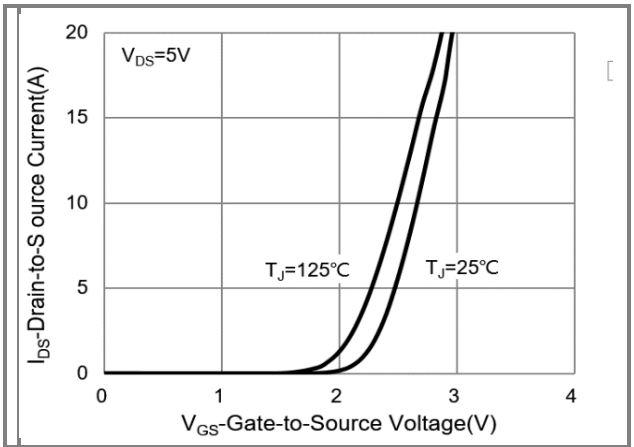

Fig.2 Transfer Characteristics

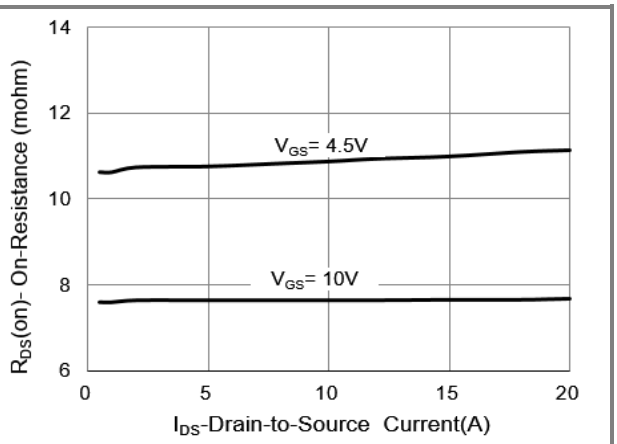

Fig.3 On-Resistance vs. Drain Current

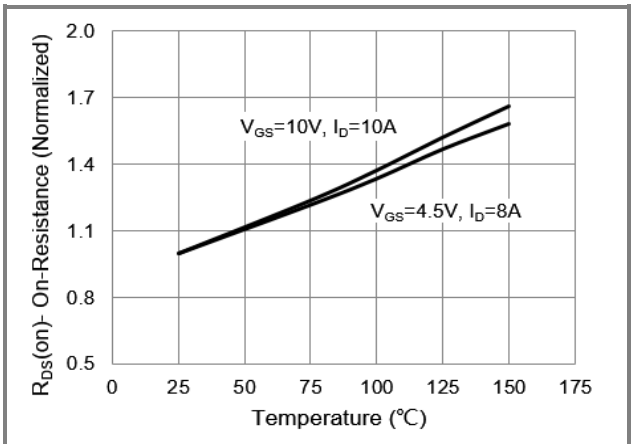

Fig.4 On-Resistance vs. Junction temperature

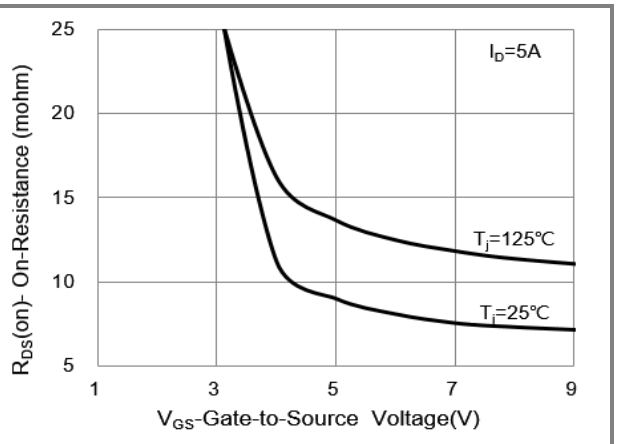

Fig.5 On-Resistance Variation with V_{GS}

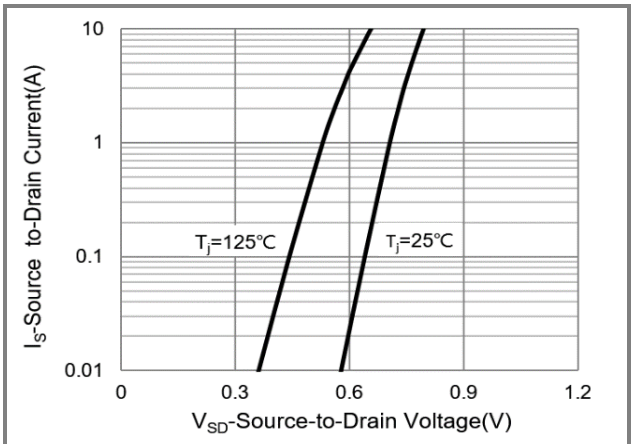

Fig.6 Body Diode Characteristics

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TYPICAL CHARACTERISTIC CURVES

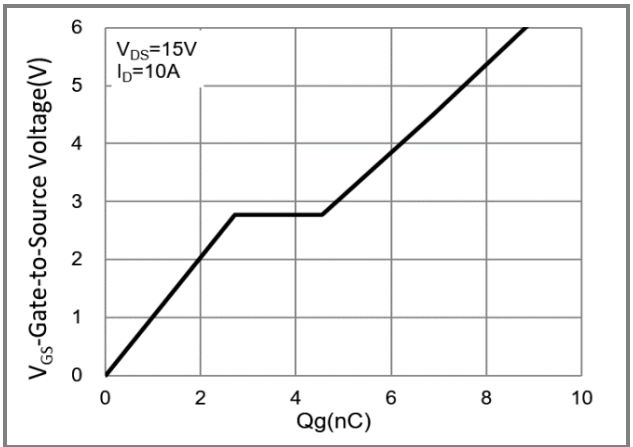


Fig.7 Gate-Charge Characteristics

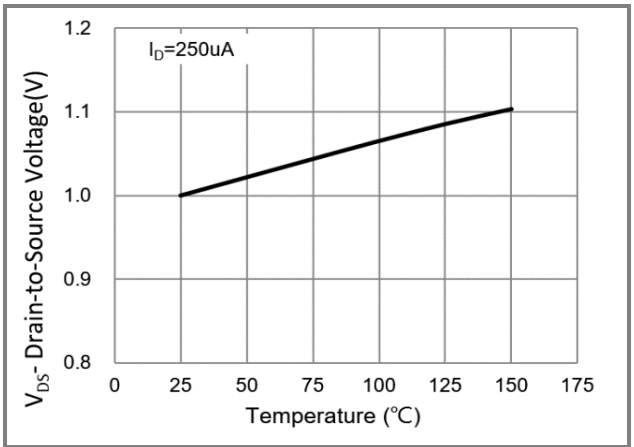


Fig.8 Breakdown Voltage Variation vs. Temperature

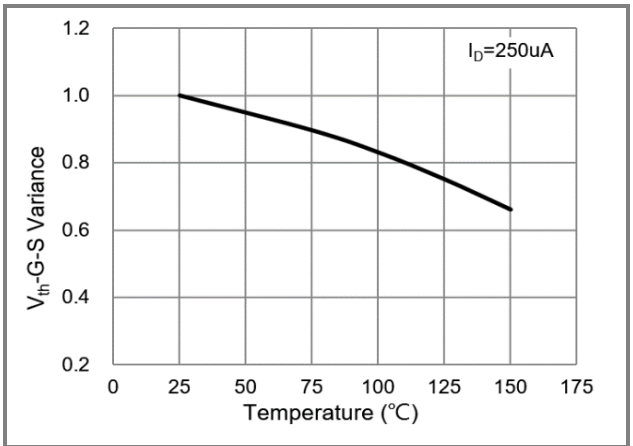


Fig.9 Threshold Voltage Variation with Temperature

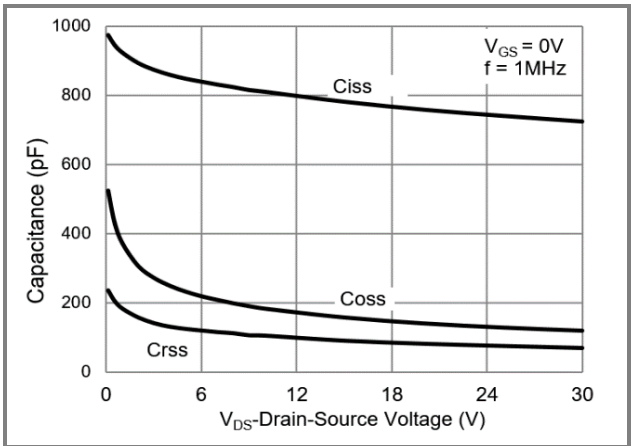


Fig.10 Capacitance vs. Drain-Source Voltage

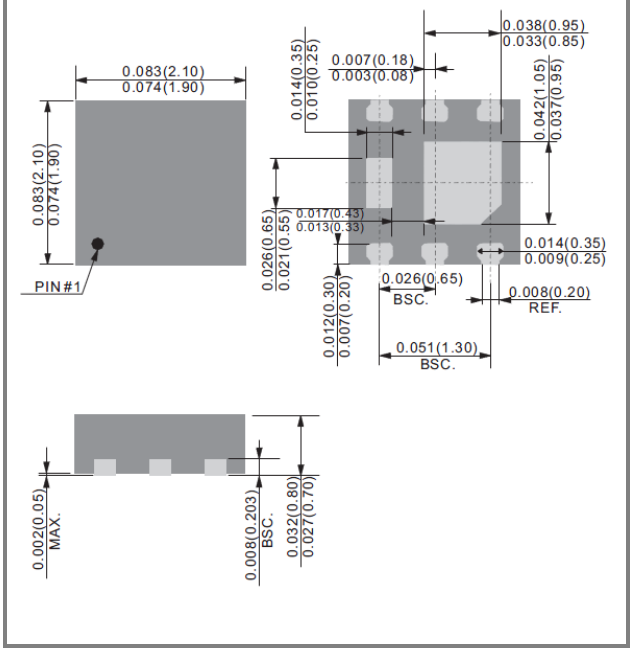
PJQ2408

Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ2408_R1_00001	DFN2020B-6L	3K pcs / 7" reel	408	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout

DFN2020B-6L Dimension — Unit: inch(mm)



DFN2020B-6L Pad Layout — Unit: inch(mm)